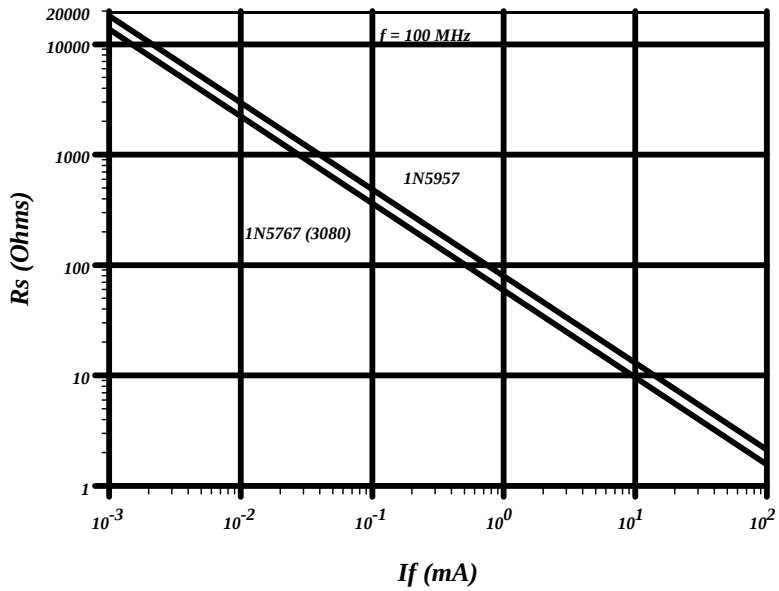
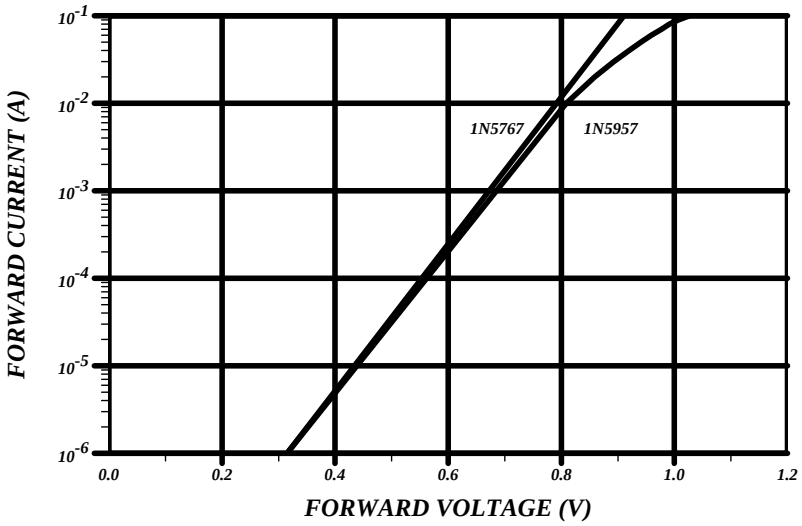
Parameter	Symbol	Conditions	1N5767	1N5957	Units
Total Capacitance (Max)	C_T	V_R=100V, F= 1 MHz	0.4	0.4	pF
Series Resistance	R_S	If = 10 µA, F= 100 MHz	1000Ω(min) 2000Ω(typ)	1500Ω(min) 3000Ω(typ)	Ohms
Series Resistance	R_S	If = 20 mA, F = 100 MHz	8Ω(max) 4Ω(typ)	8Ω(max) 6Ω(typ)	Ohms
Series Resistance	R_S	If = 100 mA, f = 100 MHz	2.5Ω(max) 1.5Ω(typ)	3.5Ω(max) 2.0Ω(typ)	Ohms
Carrier Lifetime	τ	I_F = 10 mA	1.0(min)	1.5(min) 2.0(typ)	µs
Reverse Current	I_R	V_R = Voltage rating	10(max)	10(max)	µA
Current for Rs = 75Ω	I_{75}	Rs = 75Ω	0.7	0.8 – 1.2	mA
Return Loss	-	Diode terminates 75Ω line	30(typ)	30(typ)	dB
Second Order Distortion	-	Bridged tee attenuator Attenuation = 10 dB	-40(typ)	-50(typ)	dB
Third Order Distortion	-	Pin = 50 dBmv F1 = 10 MHz F2 = 13 MHz	-60(typ)	-65(typ)	dB

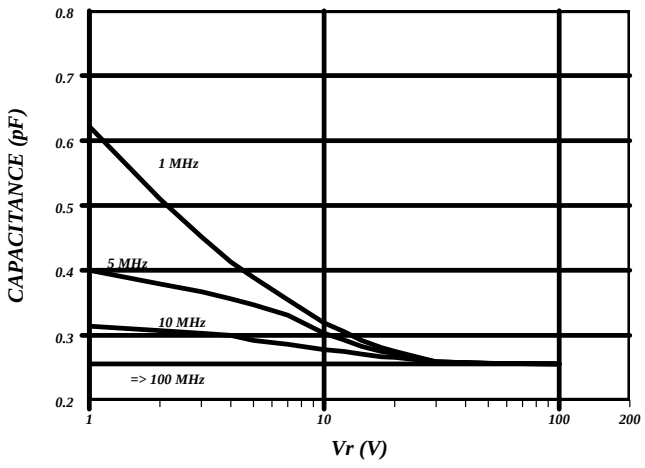
Rs versus If
TYPICAL



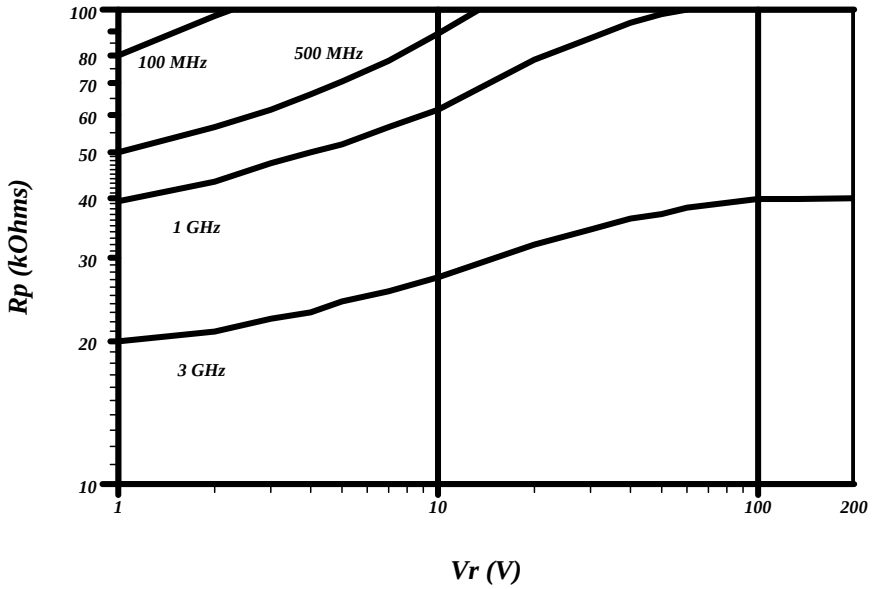
FORWARD VOLTAGE versus CURRENT



Ct versus Vr
TYPICAL



PARALLEL RESISTANCE versus REVERSE VOLTAGE
TYPICAL



NOTES:

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